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AMENDMENT TRANSMITTAL LETTER				Docket No. 8733.170.10-US	
Application No. 10/671,552-Conf. #4274		Filing Date September 29, 2003		Examiner A. G. Ghyka	
				Art Unit 2812	
Applicant(s): Kwang Nam Kim et al.					
Invention: METHOD OF FORMING SILICON OXIDE LAYER AND METHOD OF MANUFACTURING THIN FILM TRANSISTOR THEREBY					
<b>TO THE COMMISSIONER FOR PATENTS</b>					
Transmitted herewith is an amendment in the above-identified application.					
The fee has been calculated and is transmitted as shown below.					
<b>CLAIMS AS AMENDED</b>					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	10	- 20 =		x	0.00
Independent Claims	1	- 3 =		x	0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
<b>TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:</b>					0.00
<input checked="" type="checkbox"/> Large Entity <input type="checkbox"/> Small Entity					
<input checked="" type="checkbox"/> No additional fee is required for this amendment.					
<input type="checkbox"/> Please charge Deposit Account No. _____ in the amount of \$ _____. A duplicate copy of this sheet is enclosed.					
<input type="checkbox"/> A check in the amount of \$ _____ to cover the filing fee is enclosed.					
<input type="checkbox"/> Payment by credit card. Form PTO-2038 is attached.					
<input checked="" type="checkbox"/> The Director is hereby authorized to charge and credit Deposit Account No. <u>50-0911</u> as described below. A duplicate copy of this sheet is enclosed.					
<input checked="" type="checkbox"/> Credit any overpayment.					
<input checked="" type="checkbox"/> Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.					
 Rebecca Goldman Rudich Attorney Reg. No.: 41,786				Dated: <u>July 9, 2004</u>	
MCKENNA LONG & ALDRIDGE LLP 1900 K Street, N.W. Washington, DC 20006 (202) 496-7463					



Docket No.: 8733.170.10-US  
(PATENT)

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:  
Kwang Nam KIM, et al.

Confirmation No. 4274

Application No.: 10/671,552

Art Unit: 2812

Filed: September 29, 2003

Examiner: Ghyka, Alexander G.

For: METHOD OF FORMING SILICON OXIDE  
LAYER AND METHOD OF  
MANUFACTURING THIN FILM  
TRANSISTOR THEREBY

Customer No. 30827

**AMENDMENT IN RESPONSE TO NON-FINAL OFFICE ACTION**

MS Non-Fee Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

**INTRODUCTORY COMMENTS**

In response to the Office Action dated April 9, 2004 (Paper No. 0331), please amend the above-identified U.S. patent application as follows:

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper. This listing of claims replaces all prior versions and listings of claims in the application.

**Remarks/Arguments** begin on page 4 of this paper.